

## TO-252-2L Plastic-Encapsulate Transistors

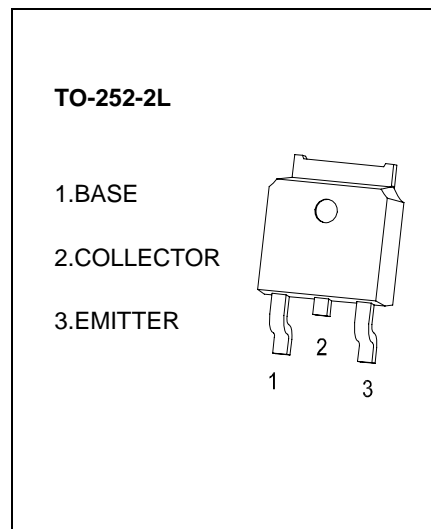
### 3CA753 TRANSISTOR (PNP)

#### FEATURES

- Power Dissipation

#### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-40	V
V <sub>CE0</sub>	Collector-Emitter Voltage	-30	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current -Continuous	-2	A
P <sub>C</sub>	Collector power dissipation	1.2	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C



#### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μA, I <sub>E</sub> =0	-40			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> =0	-30			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-1mA, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-40V, I <sub>E</sub> =0			-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0			-0.1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-500mA	100		400	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-2A, I <sub>B</sub> =-200mA			-0.8	V
	V <sub>CE(sat)</sub>	I <sub>C</sub> =-1.5A, I <sub>B</sub> =-30mA			-2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-500mA		120		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz		13		pF

#### CLASSIFICATION OF h<sub>FE</sub>

Rank	O	Y	G
Range	100-200	160-320	200-400
Marking			